

TPIC6B596 Power Logic 8-Bit Shift Register

1 Features

- Low $r_{DS(on)}$: 5Ω
- Avalanche energy: 30mJ
- Eight power DMOS-transistor outputs of 150-mA continuous current
- 500mA typical current-limiting capability
- Output clamp voltage: 50V
- Enhanced cascading for multiple stages
- All registers cleared with single input
- Low power consumption

2 Application

- Instrumentation Clusters
- Tell-Tale Lamps
- LED Illumination and Controls
- Automotive Relay or Solenoids Drivers

3 Description

The TPIC6B596 is a monolithic, high-voltage, medium-current power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

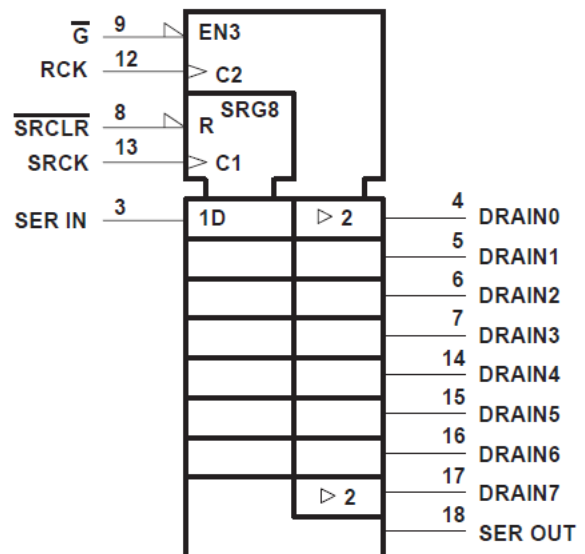
This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK), respectively. The storage register transfers data to the output buffer when shift-register clear (SRCLR) is high. Write data and read data are valid only when RCK is low. When SRCLR is low, all registers in the device are cleared. When output enable (\overline{G}) is held high, all data in the output buffers is held low and all drain outputs are off. When \overline{G} is held low, data from the storage register is transparent to the output buffers. When data in the output buffers is low, the DMOS-transistor outputs are off. When data is high, the DMOS-transistor outputs have sink-current capability. The serial output (SER OUT) is clocked out of the device on the falling edge of SRCK to provide additional hold time for cascaded applications. This will provide improved performance for applications where clock signals may be skewed, devices are not located near one another, or the system must tolerate electromagnetic interference.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50V and 150mA continuous sink-current capability. Each output provides a 500mA typical current limit at $T_C = 25^\circ\text{C}$. The current limit decreases as the junction temperature increases for additional device protection.

The TPIC6B596 is characterized for operation over the operating case temperature range of -40°C to 125°C .

Table 3-1. Device Information

PART NUMBER	PACKAGE	BODY SIZE(NOM)
TPIC6A595	PDIP(20)	25.4mm × 6.35mm
	SOIC(20)	12.80mm × 7.50mm



- A. † This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

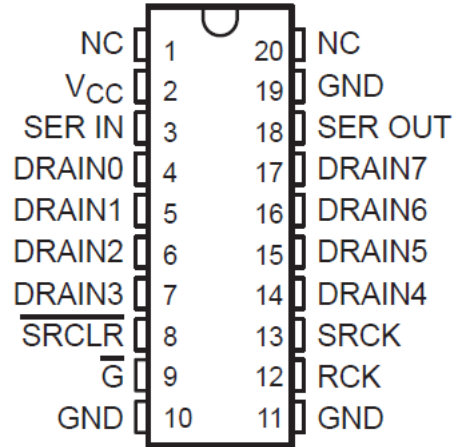
Logic Symbol



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4 Pin Configuration and Functions



A. NC - No internal connection

Figure 4-1. DW or N Package (Top View)

Pin Function

PIN		I/O	DESCRIPTION
Name	NO.		
DRAIN0	4	O	Open-drain output
DRAIN1	5		
DRAIN2	6		
DRAIN3	7		
DRAIN4	14		
DRAIN5	15		
DRAIN6	16		
DRAIN7	17		
Ḡ	9	I	Output enable, active-low
GND	10, 11, 19	-	Power ground
NC	1, 20	-	No internal connection
RCK	12	I	Register clock
SERIN	3	I	Serial data input
SEROUT	18	O	Serial data output
SRCK	13	I	Shift register clock
SRCLR	8	I	Shift register clear, active-low
VCC	2	I	Power supply

5 Specifications

5.1 Absolute Maximum Ratings

over recommended operating case temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Logic supply voltage ⁽²⁾		7	V
V _I	Logic input voltage range	-0.3	7	V
V _{DS}	Power DMOS drain-to-source voltage ⁽³⁾		50	V
	Continuous source-to-drain diode anode current		500	mA
	Pulsed source-to-drain diode anode current ⁽⁴⁾		1	A
I _D	Pulsed drain current, each output, all outputs on ⁽⁴⁾	T _C = 25°C	500	mA
I _D	Continuous drain current, each output, all outputs on	T _C = 25°C	150	mA
I _{DM}	Peak drain current single output ⁽⁴⁾	T _C = 25°C	500	mA
E _{AS}	Single-pulse avalanche energy (see Figure 6-4)		30	mJ
I _{AS}	Avalanche current ⁽⁵⁾		500	mA
	Continuous total dissipation	See Section 5.2		
T _J	Operating virtual junction temperature range	-40	150	°C
T _C	Operating case temperature range	-40	125	°C
	Storage temperature range	-65	150	°C
	Lead temperature 1,6mm (1/16 inch) from case for 10 seconds		260	°C

- (1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to GND.
- (3) Each power DMOS source is internally connected to GND.
- (4) Pulse duration ≤ 100 μs and duty cycle ≤ 2%.
- (5) DRAIN supply voltage = 15V, starting junction temperature (T_{JS}) = 25°C, L = 200mH, I_{AS} = 0.5A (see Figure 6-4).

5.2 Dissipation Rating Table

PACKAGE	T _C ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _C = 25°C	T _C = 125°C POWER RATING
DW	1389mW	11.1mW/°C	278mW
N	1050mW	10. mW/°C	263mW

5.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V _{CC}	Logic supply voltage	4.5	5.5	V
V _{IH}	High-level input voltage	0.85 V _{CC}		V
V _{IL}	Low-level input voltage		0.15 V _{CC}	V
	Pulsed drain output current, T _C = 25°C, V _{CC} = 5V ^{(1) (2)}	-500	500	mA
t _{su}	Setup time, SER IN high before SRCK (see Figure 6-2)	15		ns
t _h	Hold time, SER IN high after SRCK (see Figure 6-2)	15		ns
t _w	Pulse duration (see Figure 6-2)	40		ns
T _C	Operating case temperature	-40	125	°C

- (1) Pulse duration ≤ 100μs and duty cycle ≤ 2%.
- (2) Technique should limit T_J - T_C to 10°C maximum.

5.4 Electrical Characteristics

$V_{CC} = 5V$, $T_C = 25^\circ C$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$	Drain-to-source breakdown voltage	$I_D = 1mA$		50			V
V_{SD}	Source-to-drain diode forward voltage	$I_F = 100mA$			0.85	1	V
V_{OH}	High-level output voltage, SER OUT	$I_{OH} = -20\mu A$	$V_{CC} = 4.5V$	4.4	4.49		V
		$I_{OH} = -4mA$	$V_{CC} = 4.5V$	4	4.2		
V_{OL}	Low-level output voltage, SER OUT	$I_{OL} = 20\mu A$	$V_{CC} = 4.5V$		0.005	0.1	V
		$I_{OL} = 4mA$	$V_{CC} = 4.5V$		0.3	0.5	
I_{IH}	High-level input current	$V_{CC} = 5.5V$	$V_I = V_{CC}$			1	μA
I_{IL}	Low-level input current	$V_{CC} = 5.5V$	$V_I = 0$			-1	μA
I_{CC}	Logic supply current	$V_{CC} = 5.5V$		All outputs off	20	100	μA
				All outputs on	150	300	
$I_{CC(FRQ)}$	Logic supply current at frequency	$f_{SRCK} = 5MHz$, All outputs off,	$C_L = 30pF$, See Figure 6-2 and Figure 5-2		0.4	5	mA
I_N	Nominal current	$V_{DS(on)} = 0.5V$, $I_N = I_D$, $T_C = 85^\circ C$	See (1) (2) (3)		90		mA
I_{DSX}	Off-state drain current	$V_{DS} = 40V$	$V_{CC} = 5.5V$		0.1	5	μA
		$V_{DS} = 40V$	$V_{CC} = 5.5V$, $T_C = 125^\circ C$		0.15	8	
$r_{DS(on)}$	Static drain-source on-state resistance	$I_D = 100mA$	$V_{CC} = 4.5V$	See Figure 5-3 and Figure 5-4 (1) (2)	4.2	5.7	Ω
		$I_D = 100mA$ $V_{CC} = 4.5V$	$T_C = 125^\circ C$		6.8	9.5	
		$I_D = 350mA$	$V_{CC} = 4.5V$		5.5	8	

- (1) Technique should limit $T_J - T_C$ to $10^\circ C$ maximum.
- (2) These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- (3) Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of $0.5V$ at $T_C = 85^\circ C$.

5.5 Switching Characteristics

V_{CC} = 5V, T_C = 25°C

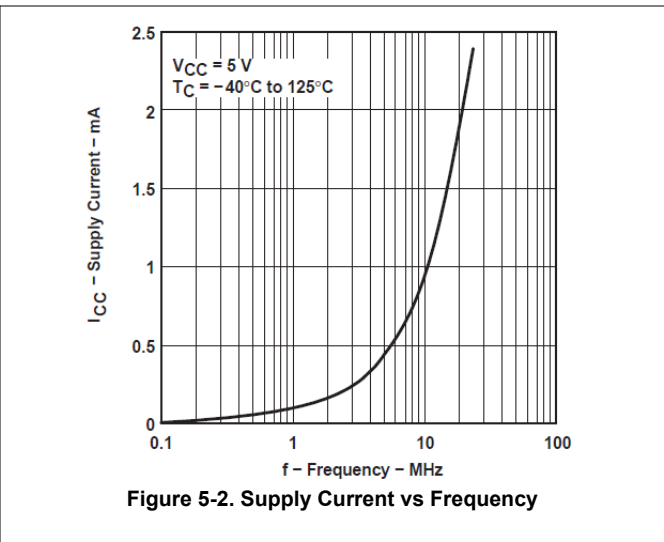
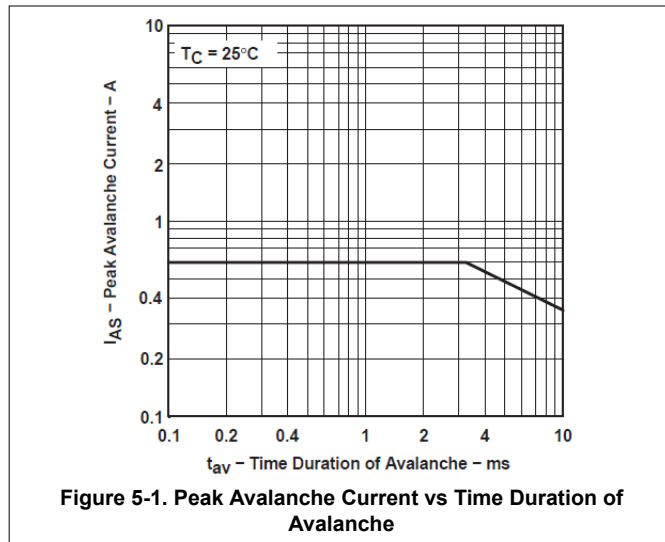
PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output from G	C _L = 30pF,	I _D = 100mA,		150		ns
t _{PHL}	Propagation delay time, high-to-low-level output from \bar{G}				90		ns
t _r	Rise time, drain output	See Figure 6-1, Figure 6-2 and Figure 5-5			200		ns
t _f	Fall time, drain output				200		ns
t _{pd}	Propagation delay time, SRCK _↓ to SEROUT	C _L = 30pF, See Figure 6-2	I _D = 100mA,		15		ns
f _(SRCK)	Serial clock frequency	C _L = 30pF, See ⁽³⁾	I _D = 100mA,			10	MHz
t _a	Reverse-recovery-current rise time	I _F = 100mA,	di/dt = 20A/μs,		100		ns
t _{rr}	Reverse-recovery time	See Figure 6-3 ⁽¹⁾ ⁽²⁾			300		

- (1) Technique should limit T_J – T_C to 10°C maximum.
- (2) These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- (3) This is the maximum serial clock frequency assuming cascaded operation where serial data is passed from one stage to a second stage. The clock period allows for SRCK → SEROUT propagation delay and setup time plus some timing margin.

5.6 Thermal Resistance

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
R _{θJA}	Thermal resistance, junction-to-ambient	DW package	All 8 outputs with equal power		90	°C/W
		N package			95	

5.7 Typical Characteristics



5.7 Typical Characteristics (continued)

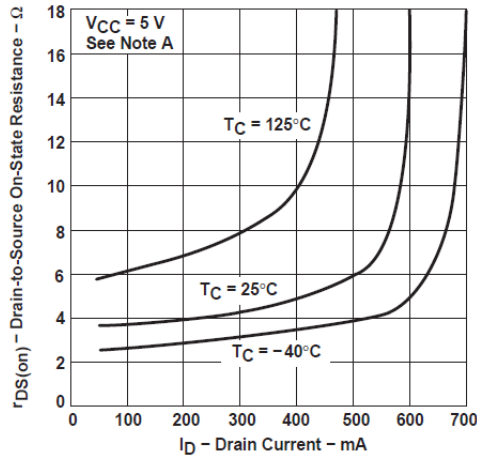


Figure 5-3. Drain-to-Source On-State Resistance vs Drain Current

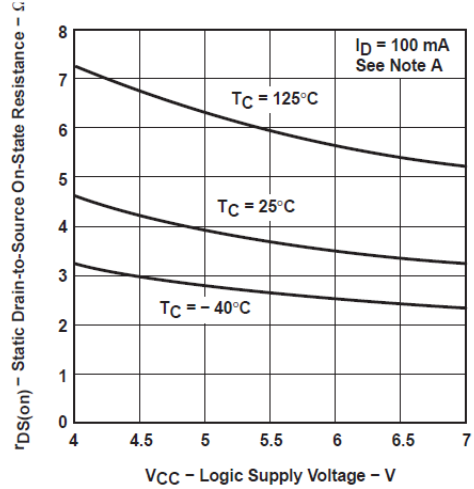
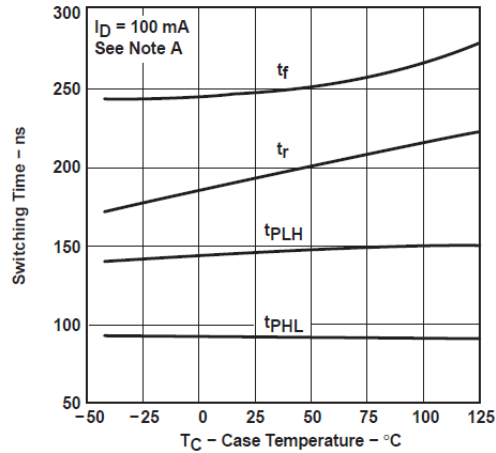


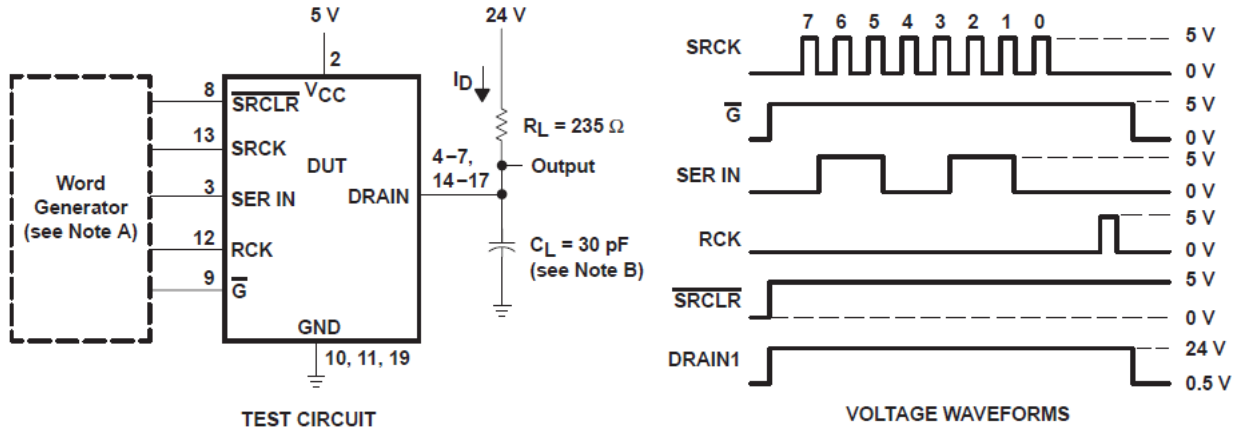
Figure 5-4. Static Drain-to-Source On-State Resistance vs Logic Supply Voltage



Technique should limit $T_J - T_C$ to 10°C maximum.

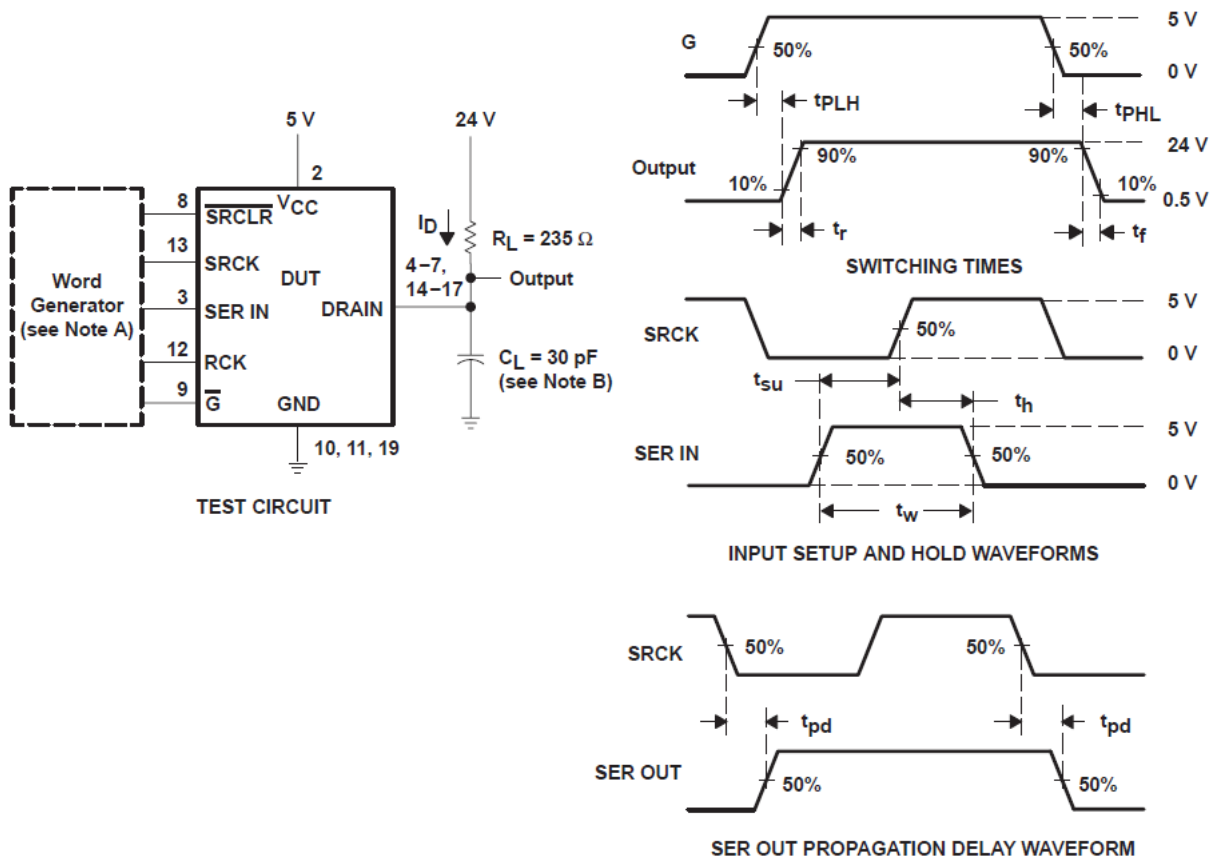
Figure 5-5. Switching Time vs Case Temperature

6 Parameter Measurement Information



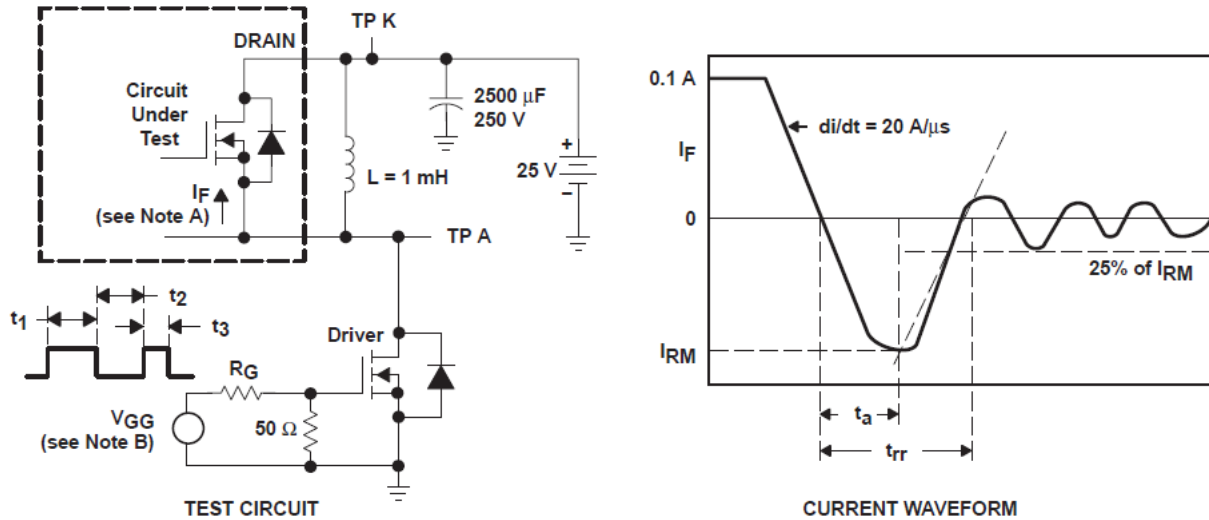
- A. The word generator has the following characteristics: $t_r \leq 10\text{ns}$, $t_f \leq 10\text{ns}$, $t_w = 300\text{ns}$, pulsed repetition rate (PRR) = 5kHz, $Z_O = 50\Omega$.
- B. C_L includes probe and jig capacitance.
- C. Write data and read data are valid only when RCK is low

Figure 6-1. Resistive-Load Test Circuit and Voltage Waveforms



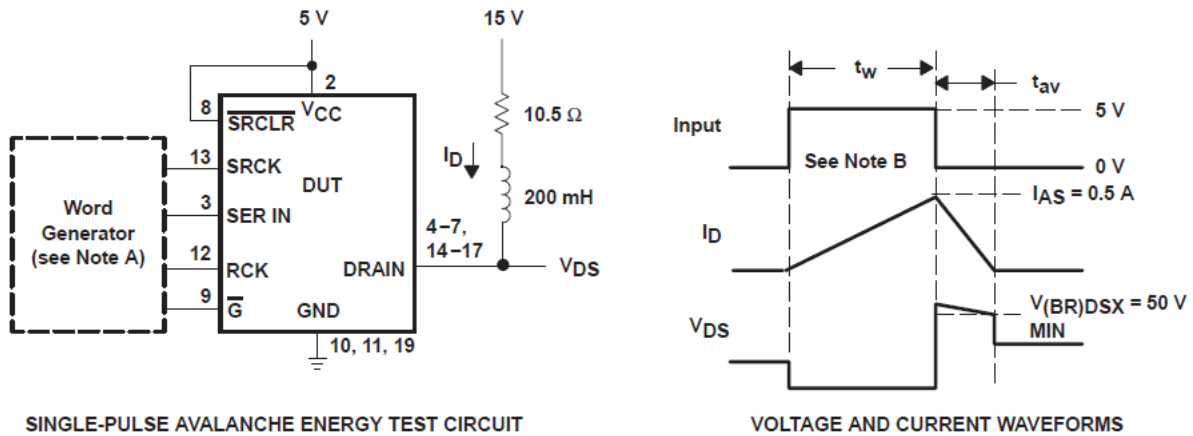
- A. The word generator has the following characteristics: $t_r \leq 10\text{ns}$, $t_f \leq 10\text{ns}$, $t_w = 300\text{ns}$, pulsed repetition rate (PRR) = 5kHz, $Z_O = 50\Omega$.
- B. C_L includes probe and jig capacitance

Figure 6-2. Test Circuit, Switching Times, and Voltage Waveforms



- A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
- B. The V_{GG} amplitude and R_G are adjusted for $di/dt = 20A/\mu s$. A V_{GG} double-pulse train is used to set $I_F = 0.1A$, where $t_1 = 10\mu s$, $t_2 = 7\mu s$, and $t_3 = 3\mu s$.

Figure 6-3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



- A. The word generator has the following characteristics: $t_r \leq 10ns$, $t_f \leq 10ns$, $Z_O = 50\Omega$.
- B. Input pulse duration, t_w , is increased until peak current $I_{AS} = 0.5A$.
Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30mJ$.

Figure 6-4. Single-Pulse Avalanche Energy Test Circuit and Waveforms

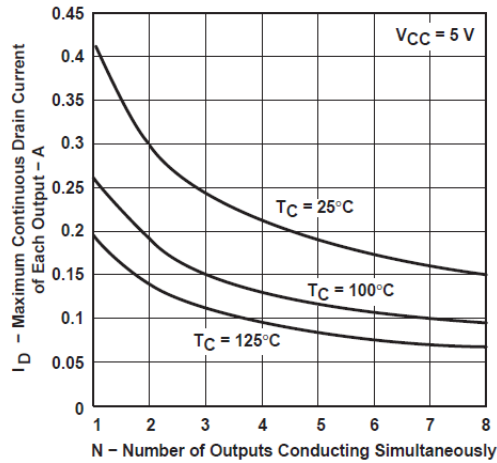


Figure 6-5. Maximum Continuous Drain Current of Each Output vs Number of Outputs Conducting Simultaneously

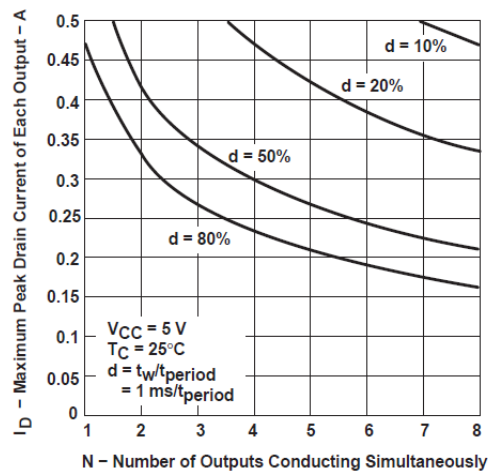


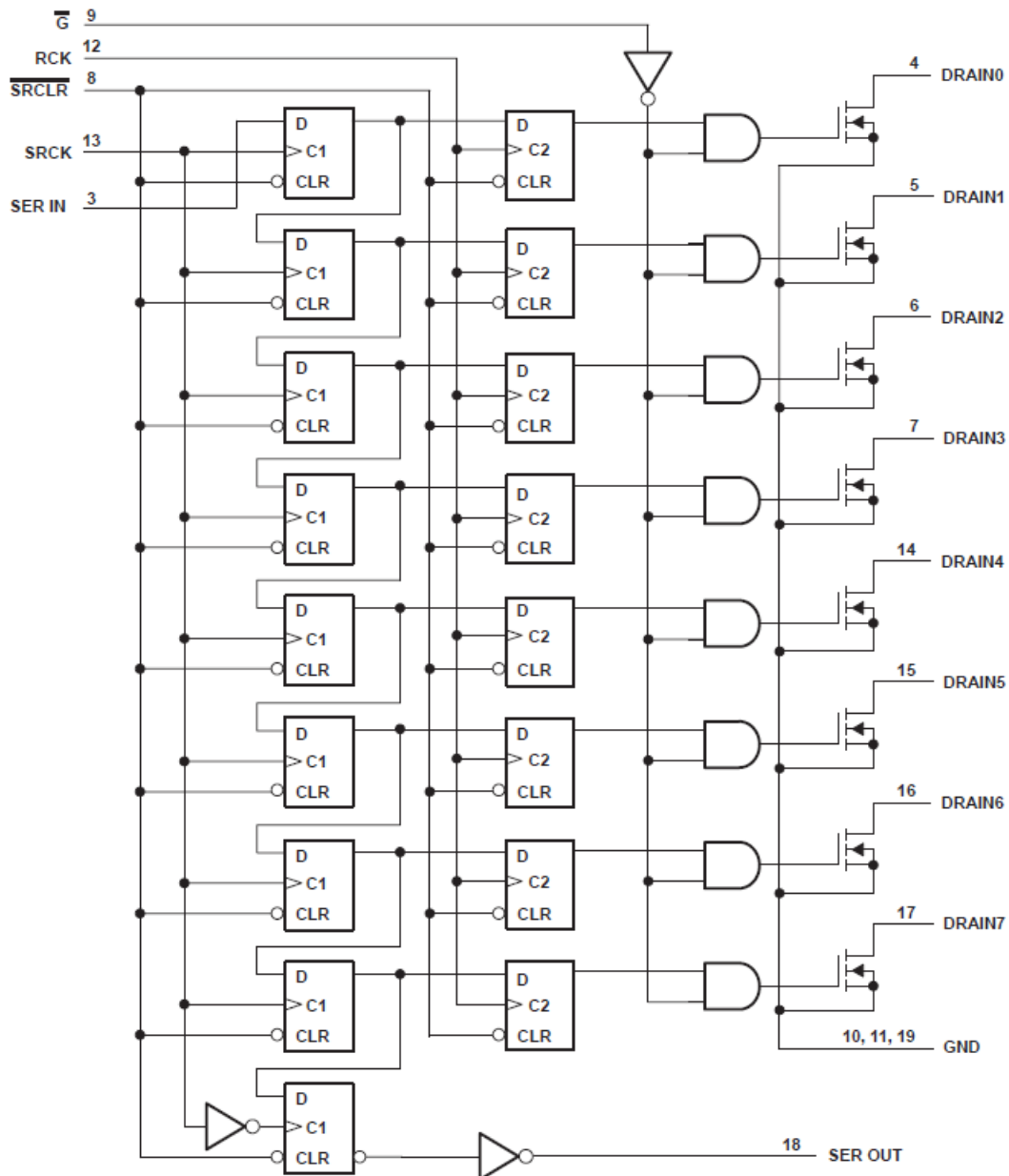
Figure 6-6. Maximum Peak Drain Current of Each Output vs Number of Outputs Conducting Simultaneously

7 Detailed Description

7.1 Overview

The TPIC6B596 device is a monolithic, high-voltage, medium-current power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection, so it can also drive relays, solenoids, and other medium-current or high-voltage loads.

7.2 Functional Block Diagram



Functional Block Diagram

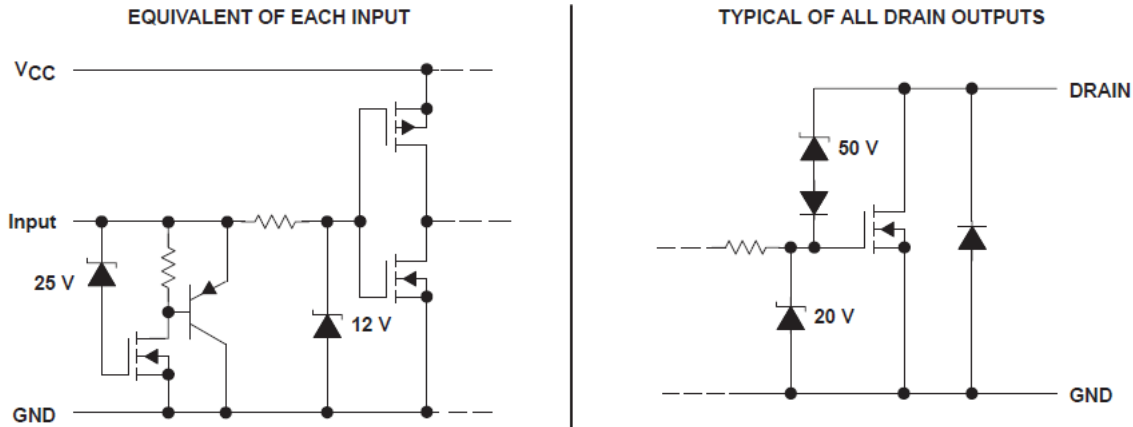


Figure 7-1. Functional Block Diagram (continued)

7.3 Reference

7.3.1 Reference

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift register clock (SRCK) and the register clock (RCK), respectively. Write data and read data are valid only when RCK is low. The storage register transfers data to the output buffer when shift register clear (SRCLR) is high.

7.3.2 Clear Register

A logical low on ($\overline{\text{SRCLR}}$) clears all registers in the device. TI suggests clearing the device during power up or initialization.

7.3.3 Output Control

Holding the output enable ($\overline{\text{G}}$) high holds all data in the output buffers low, and all drain outputs are off. Holding ($\overline{\text{G}}$) low makes data from the storage register transparent to the output buffers. When data in the output buffers is low, the DMOS transistor outputs are OFF. When data is high, the DMOS transistor outputs have sink-current capability. This pin can also be used for global PWM dimming.

7.3.4 Cascaded Application

The serial output (SER OUT) allows for cascading of the data from the shift register to additional devices. The serial output (SER OUT) is clocked out of the device on the falling edge of SRCK to provide additional hold time for cascaded applications. This will provide improved performance for applications where clock signals may be skewed, devices are not located near one another, or the system must tolerate electromagnetic interference. Connect the device (SER OUT) pin to the next device (SER IN) for daisy Chain.

7.3.5 Current Limit Function

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink current capability. Each output provides a 500-mA typical current limit at $T_C = 25^\circ\text{C}$. The current limit decreases as the junction temperature increases for additional device protection.

8 Device Functional Modes

8.1 Operating with $V_{CC} < 4.5V$

This device works normally during $4.5V \leq V_{CC} \leq 5.5V$, when operation voltage is lower than 4.5V, correct behavior of the device, including communication interface and current capability, is not assured.

8.2 Operating with $5.5V < V_{CC} \leq 7V$

The device works normally in this voltage range, but reliability issues can occur if the device works for a long time in this voltage range.

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (May 2005) to Revision B (March 2024)	Page
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- | | |
|-------------------------------------|---|
| • Updated Applications section..... | 1 |
|-------------------------------------|---|

Changes from Revision * (March 2000) to Revision A (May 2005)	Page
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- | | |
|--|---|
| • Changed SRCLR timing diagram in Figure 6-1 | 8 |
|--|---|

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPIC6B596DW	Obsolete	Production	SOIC (DW) 20	-	-	Call TI	Call TI	-40 to 125	
TPIC6B596DWG4	Obsolete	Production	SOIC (DW) 20	-	-	Call TI	Call TI	-	
TPIC6B596DWR	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6B596
TPIC6B596DWR.A	Active	Production	SOIC (DW) 20	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TPIC6B596
TPIC6B596DWRG4	Obsolete	Production	SOIC (DW) 20	-	-	Call TI	Call TI	-	TPIC6B596
TPIC6B596N	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TPIC6B596N
TPIC6B596N.A	Active	Production	PDIP (N) 20	20 TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 125	TPIC6B596N

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6B596DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
TPIC6B596DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6B596DWR	SOIC	DW	20	2000	350.0	350.0	43.0
TPIC6B596DWR	SOIC	DW	20	2000	350.0	350.0	43.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
TPIC6B596N	N	PDIP	20	20	506	13.97	11230	4.32
TPIC6B596N.A	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4220724/A 05/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

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NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

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NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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